

Seydi DoÄan

List of Publications by Year in descending order

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64
papers

11,982
citations

257101

24
h-index

149479

56
g-index

65
all docs

65
docs citations

65
times ranked

13557
citing authors

#	ARTICLE	IF	CITATIONS
1	Mobile system: detecting buried objects by magnetic anomaly method. Journal of Applied Remote Sensing, 2021, 15, .	0.6	2
2	Development of a photovoltaic panel emulator and LabVIEW-based application platform. Computer Applications in Engineering Education, 2020, 28, 1291-1310.	2.2	7
3	Detection and Imaging of Underground Objects for Distinguishing Explosives by Using a Fluxgate Sensor Array. Applied Sciences (Switzerland), 2019, 9, 5415.	1.3	4
4	Design of a multi-channel quartz crystal microbalance data acquisition system. Measurement Science and Technology, 2018, 29, 075009.	1.4	5
5	Classification of explosives materials detected by magnetic anomaly method. , 2017, , .		1
6	Design of a data acquisition system for passive detection of buried explosives. , 2017, , .		0
7	Lutentium incorporation influence on ZnO thin films coated via a sol-gel route: spin coating technique. Journal of Materials Science: Materials in Electronics, 2016, 27, 5089-5098.	1.1	2
8	Designing a portable data acquisition system for human-computer interface applications. , 2015, , .		0
9	Digital signal processing and classification study for electrooculogram signals. , 2015, , .		0
10	Characteristic evaluation on spray-deposited WFTO thin films as a function of W doping ratio. Rare Metals, 2014, 33, 433-441.	3.6	18
11	Fabrication and characterization of Al ₂ Cu ₂ ZnS ₄ heterojunction photodiodes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 580-586.	0.8	31
12	Structural characterizations and optical properties of InSe and InSe:Ag semiconductors grown by Bridgman/Stockbarger technique. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 64, 106-111.	1.3	39
13	An investigation of the Nb doping effect on structural, morphological, electrical and optical properties of spray deposited F doped SnO ₂ films. Physica Scripta, 2013, 87, 035602.	1.2	42
14	W doped SnO ₂ growth via sol-gel routes and characterization: Nanocubes. Optik, 2013, 124, 4827-4831.	1.4	27
15	Growth and characterization of Ag/n-ZnO/p-Si/Al heterojunction diode by sol-gel spin technique. Journal of Alloys and Compounds, 2013, 550, 129-132.	2.8	69
16	Effect of Nb doping on structural, electrical and optical properties of spray deposited SnO ₂ thin films. Superlattices and Microstructures, 2013, 56, 107-116.	1.4	98
17	A study on characterization of Al/ZnS/p-Si/Al heterojunction diode synthesized by sol-gel technique. Materials Letters, 2013, 102-103, 106-108.	1.3	26
18	Evaluation of Structural and Optical Properties of Mn-Doped ZnO Thin Films Synthesized by Sol-Gel Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2012, 43, 5088-5095.	1.1	19

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19	Investigation of structural and optical properties of ZnO films co-doped with fluorine and indium. Superlattices and Microstructures, 2012, 52, 107-115.	1.4	77
20	Structural and optical properties of ZnO thin films by the spin coating Sol-Gel method. Journal of Sol-Gel Science and Technology, 2011, 60, 66-70.	1.1	11
21	Capacitance and conductanceâ€“frequency characteristics of Auâ€“Sb/p-GaSe:Gd Schottky barrier diode. Vacuum, 2011, 85, 798-801.	1.6	26
22	Electrical characterization of Ag/p-GaSe:Gd schottky barrier diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1958-1962.	1.3	12
23	InAlN/GaN heterostructure field-effect transistors on Fe-doped semi-insulating GaN substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 908-911.	0.6	7
24	Photoionization study of deep centers in GaNâ€“AlGaIn multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3110-C3112.	0.6	0
25	Temperature-dependent electrical characterization of nitrogen-doped ZnO thin film: vacuum annealing effect. Physica Scripta, 2009, 79, 035701.	1.2	7
26	Electrical characteristics and inhomogeneous barrier analysis of Auâ€“Be/p-InSe:Cd Schottky barrier diodes. Microelectronic Engineering, 2009, 86, 106-110.	1.1	10
27	Temperature variation of currentâ€“voltage characteristics of Au/Ni/n-GaN Schottky diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 646-651.	1.3	53
28	Temperature dependent capacitance and DLTS studies of Ni/n-type 6H-SiC Schottky diode. Current Applied Physics, 2009, 9, 1181-1185.	1.1	10
29	Urbach tail and electric field influence on optical properties of InSe and InSe:Er single crystals. Applied Physics A: Materials Science and Processing, 2008, 90, 479-485.	1.1	11
30	The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. Applied Physics A: Materials Science and Processing, 2008, 91, 337-340.	1.1	26
31	The effects of the temperature and annealing on currentâ€“voltage characteristics of Ni/n-type 6Hâ€“SiC Schottky diode. Microelectronic Engineering, 2008, 85, 631-635.	1.1	31
32	Direct recognition of non-radiative recombination centers in semi-insulating LEC InP:Fe using double excitation photoluminescence. Journal of Luminescence, 2008, 128, 232-238.	1.5	8
33	Determination of the transport mechanisms in mixed conduction of reactively sputtered ZnO thin films. Journal Physics D: Applied Physics, 2008, 41, 135309.	1.3	2
34	Observation of surface charging at the edge of a Schottky contact. IEEE Electron Device Letters, 2006, 27, 211-213.	2.2	14
35	Comparison of deep levels in GaN grown by MBE, MOCVD, and HVPE. , 2005, , .		13
36	High efficiency n-ZnO/p-SiC heterostructure photodiodes grown by plasma-assisted molecular-beam epitaxy. Superlattices and Microstructures, 2005, 38, 439-445.	1.4	22

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37	Forward-current electroluminescence from GaN/ZnO double heterostructure diode. Solid-State Electronics, 2005, 49, 1693-1696.	0.8	24
38	A comprehensive review of ZnO materials and devices. Journal of Applied Physics, 2005, 98, 041301.	1.1	9,857
39	Characterization of MOCVD grown GaN on porous SiC templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2087-2090.	0.8	7
40	Deep levels in KOH etched and MOCVD regrown GaN p-n junctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2454-2457.	0.8	0
41	A study of GaN regrowth on the micro-faceted GaN template formed by in-situ thermal etching. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 718-721.	0.8	15
42	Reduction of threading dislocations in GaN overgrowth by MOCVD on TiN porous network templates. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 749-753.	0.8	5
43	Surface charging and current collapse in an AlGaIn-GaN heterostructure field effect transistor. Applied Physics Letters, 2005, 86, 083506.	1.5	21
44	Effectiveness of TiN porous templates on the reduction of threading dislocations in GaN overgrowth by organometallic vapor-phase epitaxy. Applied Physics Letters, 2005, 86, 043108.	1.5	55
45	Effect of n+-GaIn subcontact layer on 4H-SiC high-power photoconductive switch. Applied Physics Letters, 2005, 86, 261108.	1.5	27
46	Photoresponse of n-ZnO-p-SiC heterojunction diodes grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 241108.	1.5	140
47	Effects of hydrostatic and uniaxial stress on the Schottky barrier heights of Ga-polarity and N-polarity n-GaN. Applied Physics Letters, 2004, 84, 2112-2114.	1.5	45
48	Investigation of forward and reverse current conduction in GaN films by conductive atomic force microscopy. Applied Physics Letters, 2004, 84, 4150-4152.	1.5	56
49	Determination of the carrier concentration in InGaAsN-GaAs single quantum wells using Raman scattering. Applied Physics Letters, 2004, 85, 4905-4907.	1.5	8
50	Thermal stability of electron traps in GaN grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 4058-4060.	1.5	15
51	Surface band bending in as-grown and plasma-treated n-type GaN films using surface potential electric force microscopy. Applied Physics Letters, 2004, 84, 3070-3072.	1.5	42
52	The effect of hydrogen etching on 6H-SiC studied by temperature-dependent current-voltage and atomic force microscopy. Applied Physics Letters, 2004, 85, 1547-1549.	1.5	38
53	Excitonic fine structure and recombination dynamics in single-crystalline ZnO. Physical Review B, 2004, 70, .	1.1	662
54	p-GaN-i-GaN/AlGaIn multiple-quantum well n-AlGaIn back-illuminated ultraviolet detectors. Journal of Electronic Materials, 2003, 32, 307-311.	1.0	7

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55	GaN/AlGaIn back-illuminated multiple-quantum-well Schottky barrier ultraviolet photodetectors. Solid-State Electronics, 2003, 47, 1401-1408.	0.8	24
56	Electric field influence on absorption measurement in InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 274-279.	1.3	20
57	Convertibility of conductivity type in reactively sputtered ZnO thin films. Physica Status Solidi A, 2003, 195, 165-170.	1.7	16
58	4H α -SiC photoconductive switching devices for use in high-power applications. Applied Physics Letters, 2003, 82, 3107-3109.	1.5	93
59	Improvement of n-GaN Schottky diode rectifying characteristics using KOH etching. Applied Physics Letters, 2003, 82, 3556-3558.	1.5	31
60	Temperature Dependence of Magnetoresistance and Hall Effect for Ho Doped n-Type InSe. Physica Scripta, 2000, 62, 92-96.	1.2	4
61	In situ optical assessment of semi-insulating iron doped InP grown by liquid encapsulated Czochralski process. Journal of Applied Physics, 1999, 85, 6777-6781.	1.1	8
62	Growth and Temperature Dependence of Optical Properties of Er Doped and Undoped n-Type InSe. Japanese Journal of Applied Physics, 1999, 38, 5133-5136.	0.8	25
63	Anomalous Behaviour of Galvanomagnetic Effects in Very Lightly n-Type Bulk GaAs: Possible Role of Reverse-Contrast Centres. Physica Status Solidi A, 1999, 174, 467-475.	1.7	4
64	Current conduction mechanisms of heteroepitaxial and homoepitaxial GaN films grown by MBE. , 0, , .		0